

High-speed double diode

BAW56W

FEATURES

- Very small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

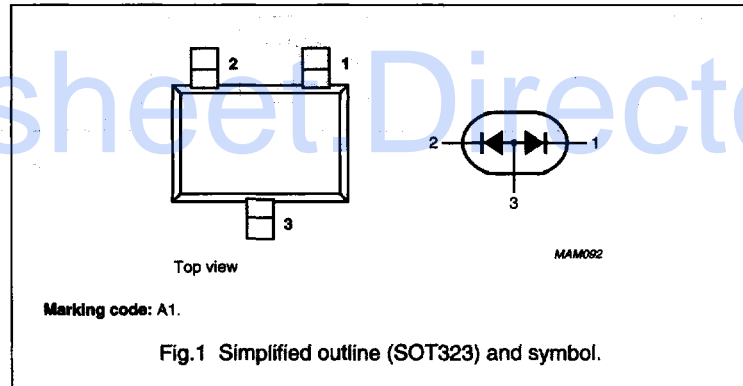
- High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

The BAW56W consists of two high-speed switching diodes with common anodes, fabricated in planar technology, and encapsulated in the very small plastic SMD SOT323 package

PINNING

PIN	DESCRIPTION
1	cathode (k1)
2	cathode (k2)
3	common anode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	single diode loaded; see Fig.2; note 1	–	150	mA
		double diode loaded; see Fig.2; note 1	–	130	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_J = 25\text{ °C}$ prior to surge; see Fig.4			
		$t = 1\ \mu\text{s}$	–	4	A
		$t = 1\ \text{ms}$	–	1	A
		$t = 1\ \text{s}$	–	0.5	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_J	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

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ELECTRICAL CHARACTERISTICS

 $T_j = 25\text{ }^\circ\text{C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_F	forward voltage	see Fig.3			
		$I_F = 1\text{ mA}$	–	715	mV
		$I_F = 10\text{ mA}$	–	855	mV
		$I_F = 50\text{ mA}$	–	1	V
		$I_F = 150\text{ mA}$	–	1.25	V
I_R	reverse current	see Fig.5			
		$V_R = 25\text{ V}$	–	30	nA
		$V_R = 75\text{ V}$	–	1	μA
		$V_R = 25\text{ V}; T_j = 150\text{ }^\circ\text{C}$	–	30	μA
		$V_R = 75\text{ V}; T_j = 150\text{ }^\circ\text{C}$	–	50	μA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	–	2.0	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}; R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	–	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10\text{ mA}$; $t_r = 20\text{ ns}$; see Fig.8	–	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		300	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

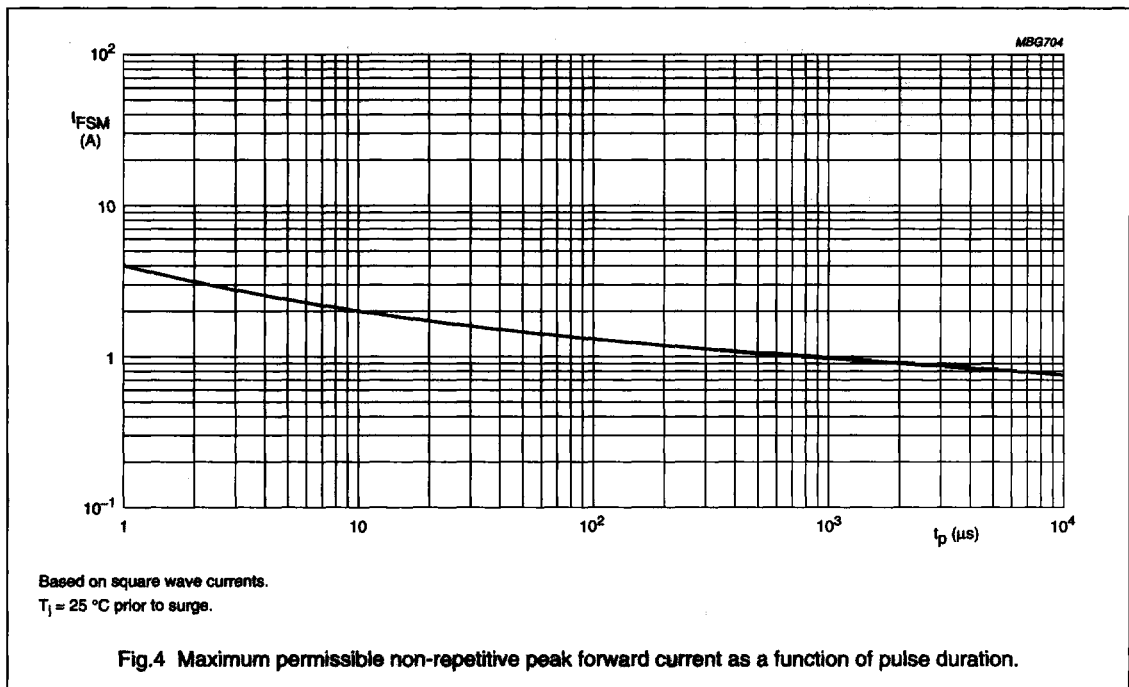
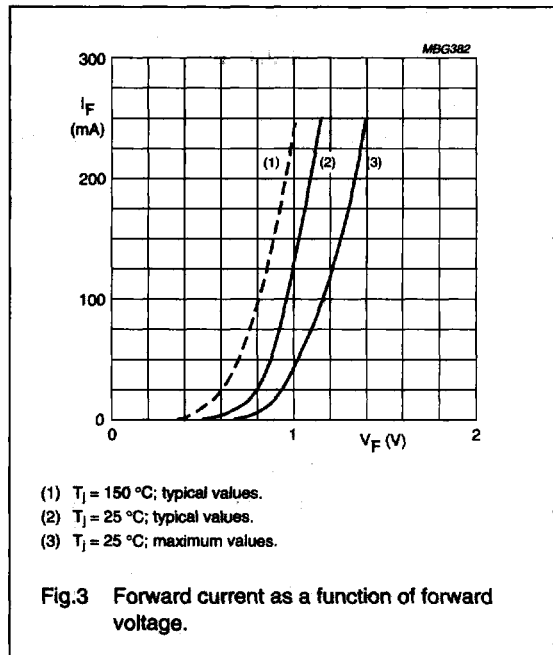
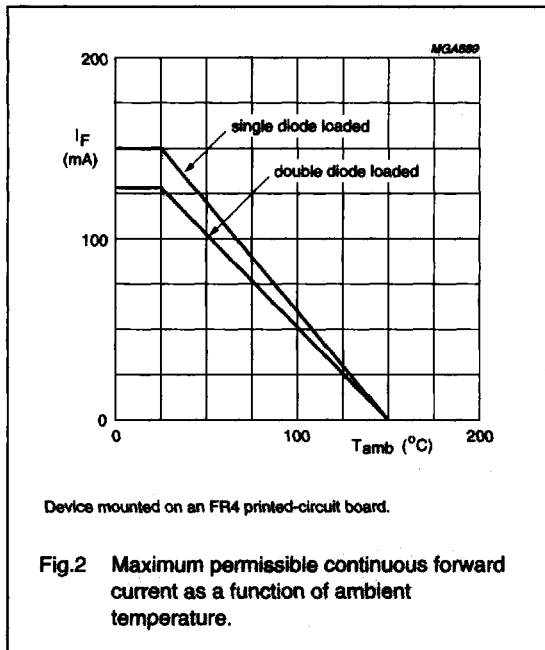
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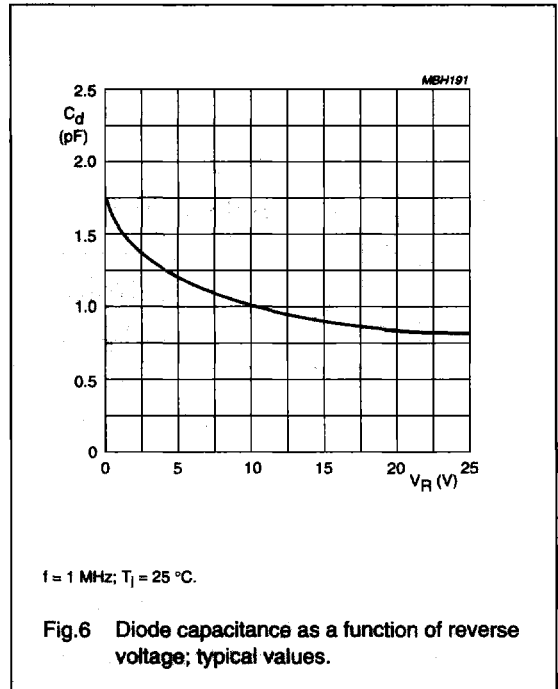
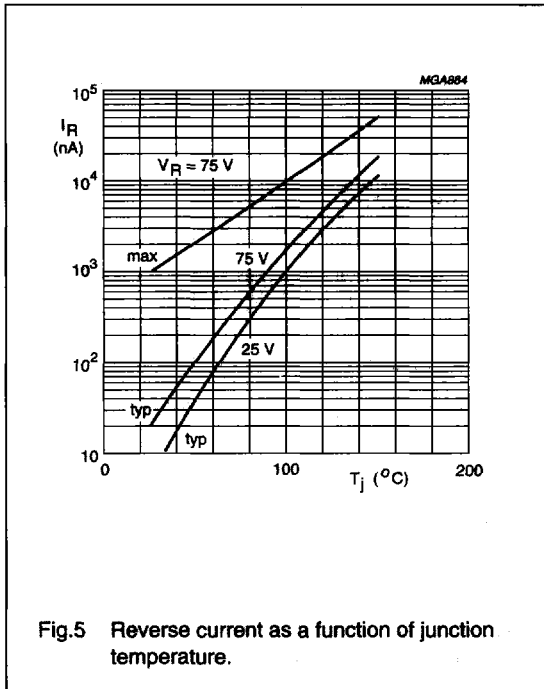
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GRAPHICAL DATA



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